

1. Material Substrate GaAs (N Type)
Epitaxial Layer GaAlAs (P/N Type)

2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbo	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F		1.5	1.55	V	IF=100mA
Reverse Voltage	V_R	8			V	IR=10uA
Power	P_O	20	25		mW	IF=100mA
Wavelength	λ_P		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data (a) Emission Area ----- 13.0mil x 13.0mil
 (b) Bottom Area ----- 14.0mil x 14.0mil
 (a) Emission Area ----- 130um
 (a) Emission Area ----- 11mil
 (e) Junction Height ----- 6.7mil

